



450V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	RDS(ON) Max	I _D T _C = +25°C
-450V	4.9Ω @ $V_{GS} = -10V$	-4.7A

Description

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- DC-DC Converters
- Power Management Functions
- Uninterrupted Power Supply

Features

- Low Input Capacitance
- High BV_{DSS} Rating for Power Application
- Low Input/Output Leakage
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

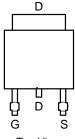
Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 3
- Weight: 0.33 grams (Approximate)

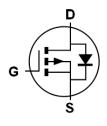




Top View



Top View



Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP45H4D9HK3-13	TO252 (DPAK)	2,500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



○ | | = Manufacturer's Marking
 45H4D9 = Product Type Marking Code
 YYWW = Date Code Marking
 YY or <u>YY</u> = Last Two Digits of Year (ex: 17 = 2017)
 WW or <u>WW</u> = Week Code (01 to 53)



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-450	V
Gate-Source Voltage	V _{GSS}	±30	V
Continuous Drain Current (Note 5) V _{GS} = -10V	ID	-4.7 -3.0	А
Maximum Body Diode Forward Current (Note 5)	Is	-1.5	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	-4.5	Α
Avalanche Current, L = 60mH (Note 7)	I _{AS}	-2.5	Α
Avalanche Energy, L = 60mH (Note 7)	E _{AS}	187	mJ

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Total Power Dissipation (Note 5)	$T_C = +25$ °C	D-	104	- W	
Total Fower Dissipation (Note 3)	$T_{C} = +100^{\circ}C$	P _D	41		
Thermal Resistance, Junction to Ambient (Note 6)		$R_{ hetaJA}$	41	°C/W	
Thermal Resistance, Junction to Case (Note 5)		$R_{ heta JC}$	1.2	C/VV	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

Electrical Characteristics (@ $T_A = \pm 25$ °C, unless otherwise specified.)

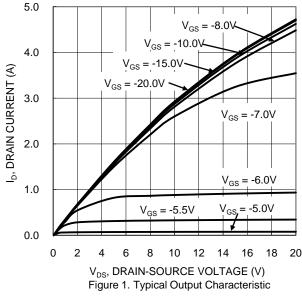
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)	Symbol	IVIIII	Тур	IVIAX	Unit	rest Condition	
` ,			T	1		I	
Drain-Source Breakdown Voltage	BV _{DSS}	-450			V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μΑ	$V_{DS} = -450V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS	_	_	±100	nA	$V_{GS} = \pm 30V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)	ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	-3.0	-4.0	-5.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	3.1	4.9	Ω	$V_{GS} = -10V, I_D = -1.05A$	
Diode Forward Voltage	V_{SD}	_	_	-1.4	V	$V_{GS} = 0V, I_{S} = -2.1A$	
Forward Transconductance	gfs	_	1.4	_	S	$V_{DS} = -50.0V, I_{D} = -1.05A$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	Ciss	_	564	_		V _{DS} = -25V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance	Coss	_	70	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	3.3	_			
Total Gate Charge (V _{GS} = -10V)	Qg	_	13.7	_		V _{DS} = -360V, I _D = -2.7A, V _{GS} = -10V	
Gate-Source Charge	Q_{gs}	_	3.4	_	nC		
Gate-Drain Charge	Q_{qd}	_	6.0	_			
Turn-On Delay Time	t _{D(ON)}	_	21	_		V_{DD} = -225V, R_G = 3.0 Ω , I_D = -2.7A	
Turn-On Rise Time	t _R	_	54	_			
Turn-Off Delay Time	t _{D(OFF)}	_	34	_	ns		
Turn-Off Fall Time	t _F	_	34	_			
Body Diode Reverse Recovery Time	t _{RR}		168	_	ns	$V_{GS} = 0V$, $V_{DD} = -200V$, $I_{S} = -2.7A$,	
Body Diode Reverse Recovery Charge	Q _{RR}		1.3	_	μC	dI/dt = 100A/μs	

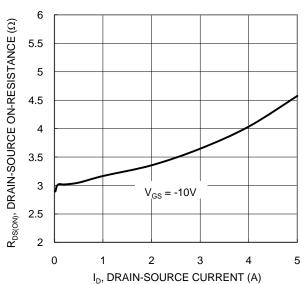
Notes:

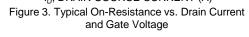
- 5. Device mounted on infinite heatsink.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.
- 7. Guaranteed by design. Not subject to production testing. 8. Short duration pulse test used to minimize self-heating effect.











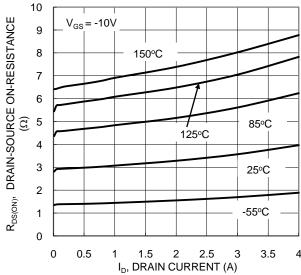
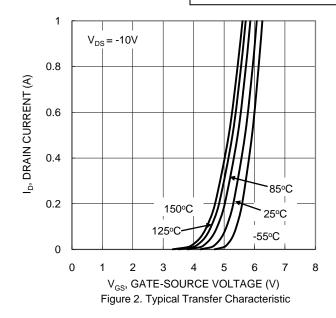
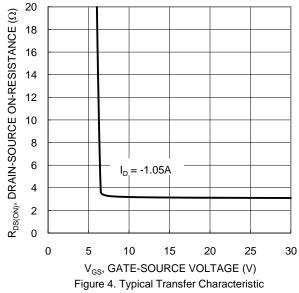
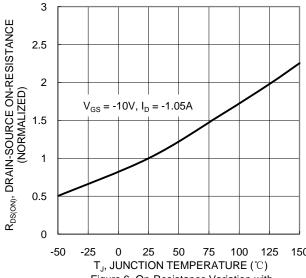


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

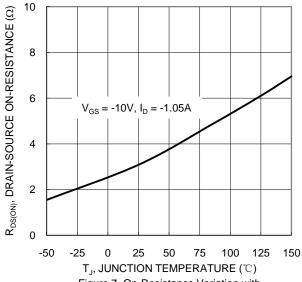


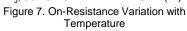


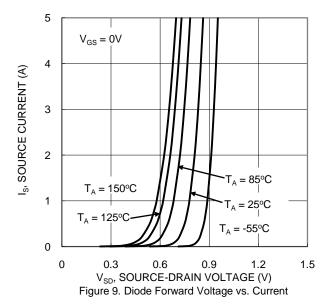


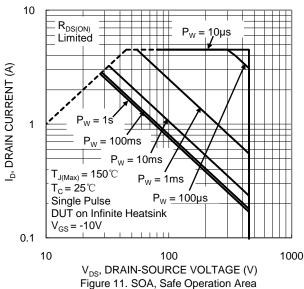












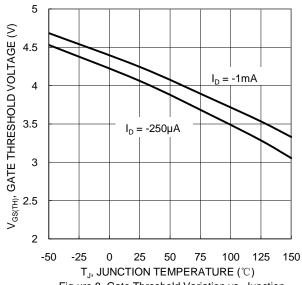
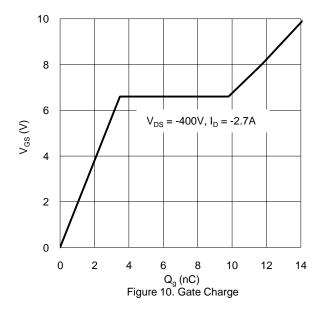
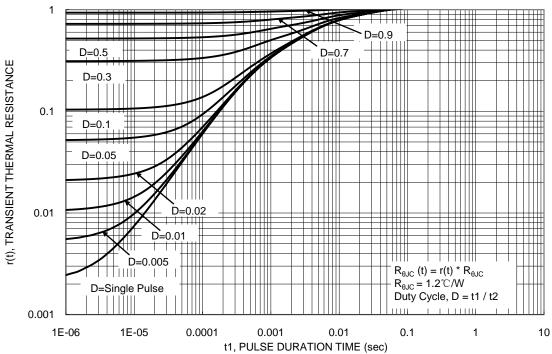


Fig.ure 8. Gate Threshold Variation vs. Junction Temperature





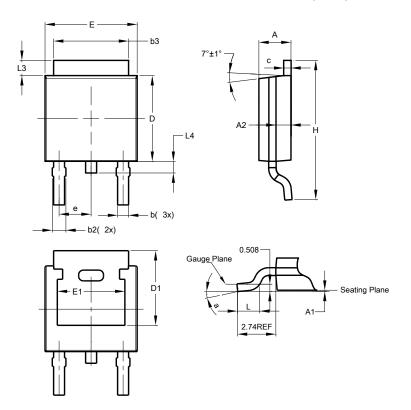




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)

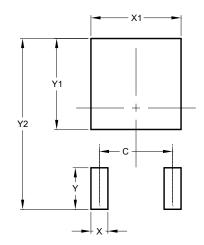


TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
Н	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)		
С	4.572		
Х	1.060		
X1	5.632		
Y	2.600		
Y1	5.700		
Y2	10.700		



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